

# FX6ASJ-2

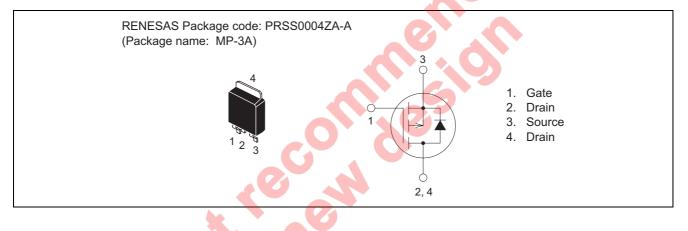
High-Speed Switching Use Pch Power MOS FET

> REJ03G1438-0200 (Previous: MEJ02G0279-0101) Rev.2.00 Aug 07, 2006

### Features

- Drive voltage : 4 V
- V<sub>DSS</sub> : 100 V
- $r_{DS(ON)(max)} : 0.58 \Omega$
- $I_D : -6 A$
- Integrated Fast Recovery Diode (TYP.): 80 ns

### Outline



### Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

### **Maximum Ratings**

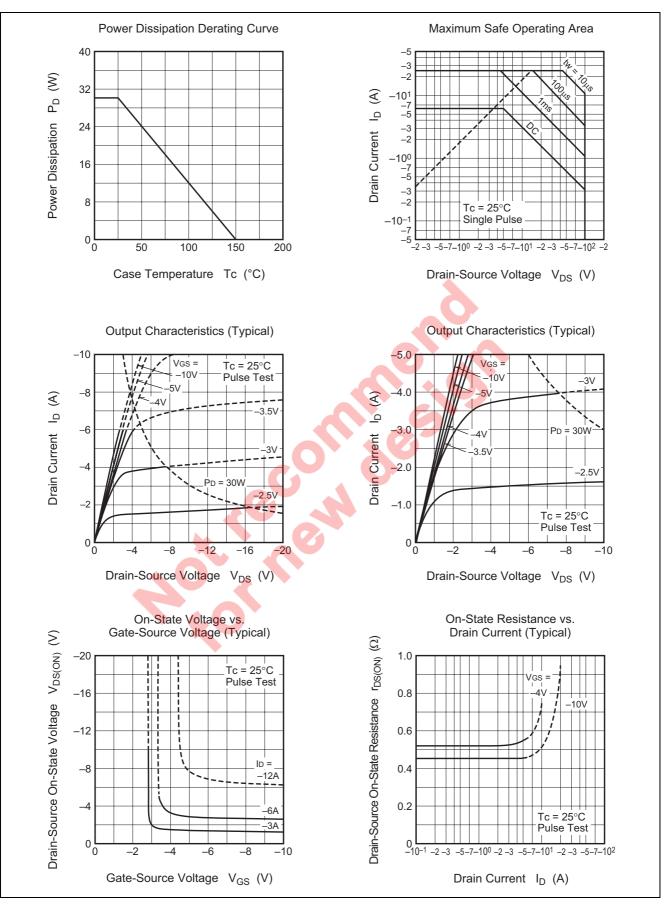
				$(\mathrm{Tc} = 25^{\circ}\mathrm{C})$	
Parameter	Symbol	Ratings	Unit	Conditions	
Drain-source voltage	V <sub>DSS</sub>	-100	V	$V_{GS} = 0 V$	
Gate-source voltage	V <sub>GSS</sub>	±20	V	$V_{DS} = 0 V$	
Drain current	I <sub>D</sub>	-6	А		
Drain current (Pulsed)	I <sub>DM</sub>	-24	А		
Avalanche drain current (Pulsed)	I <sub>DA</sub>	-6	А	L = 100 μH	
Source current	Is	-6	А		
Source current (Pulsed)	I <sub>SM</sub>	-24	А		
Maximum power dissipation	PD	30	W		
Channel temperature	Tch	- 55 to +150	°C		
Storage temperature	Tstg	- 55 to +150	°C		
Mass		0.32	g	Typical value	



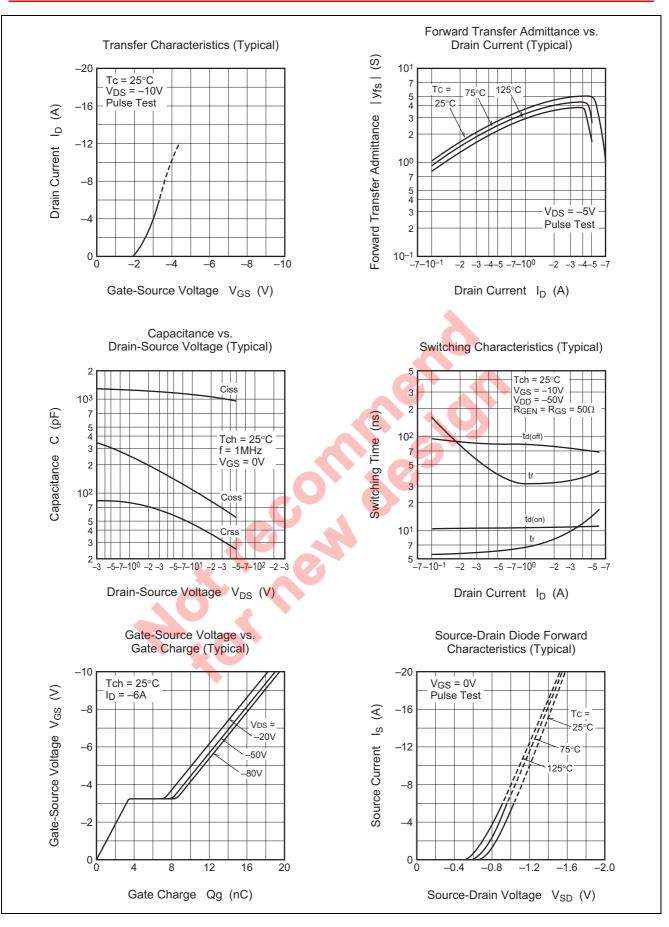
### **Electrical Characteristics**

						$(Tch = 25^{\circ}C)$
Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-100	—	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I <sub>GSS</sub>	—	—	±0.1	μA	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V
Drain-source leakage current	I <sub>DSS</sub>	—	—	-0.1	mA	$V_{DS} = -100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$
Gate-source threshold voltage	V <sub>GS(th)</sub>	-1.3	-1.8	-2.3	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.46	0.58	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.55	0.72	Ω	$I_D = -3 \text{ A}, V_{GS} = -4 \text{ V}$
Drain-source on-state voltage	V <sub>DS(ON)</sub>	—	-1.38	-1.74	V	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y <sub>fs</sub>	—	4.7	_	S	$I_D = -3 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss	—	1110	_	pF	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$
Output capacitance	Coss	—	108	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	—	44	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	9	_	ns	$V_{DD} = -50 \text{ V}, \text{ I}_{D} = -3 \text{ A},$
Rise time	tr	—	8	_	ns	$V_{GS} = -10 V$ ,
Turn-off delay time	t <sub>d(off)</sub>	—	72		ns	$R_{GEN} = R_{GS} = 50 \ \Omega$
Fall time	t <sub>f</sub>	—	33	—	ns	
Source-drain voltage	V <sub>SD</sub>	—	-1.0	-1.5	V	$I_{S} = -3 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	R <sub>th(ch-c)</sub>	—	—	4.17	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	—	80		ns	l <sub>S</sub> = −6 A, d <sub>is</sub> /d <sub>t</sub> = 100 A/μs

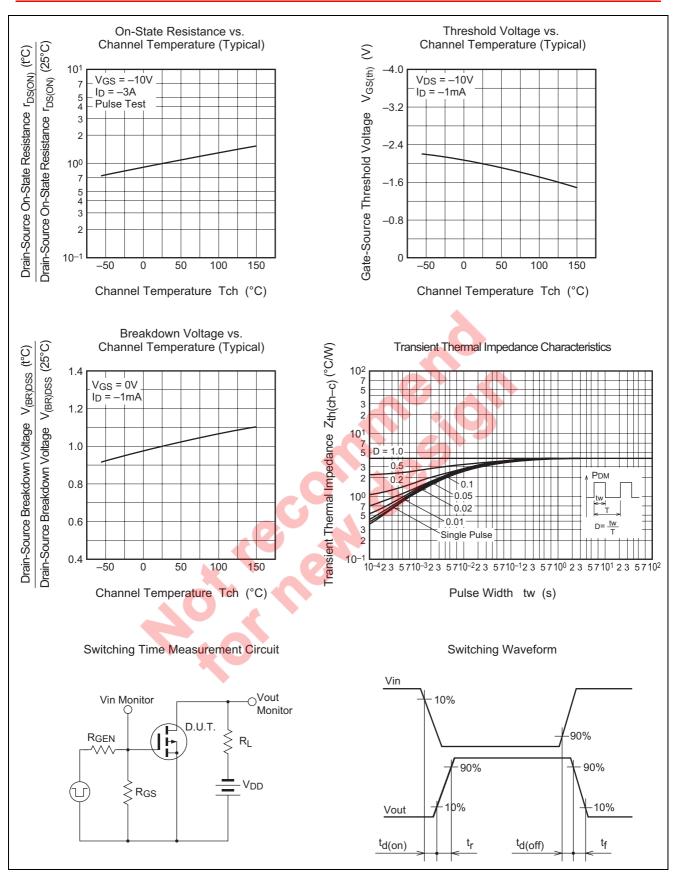
### **Performance Curves**





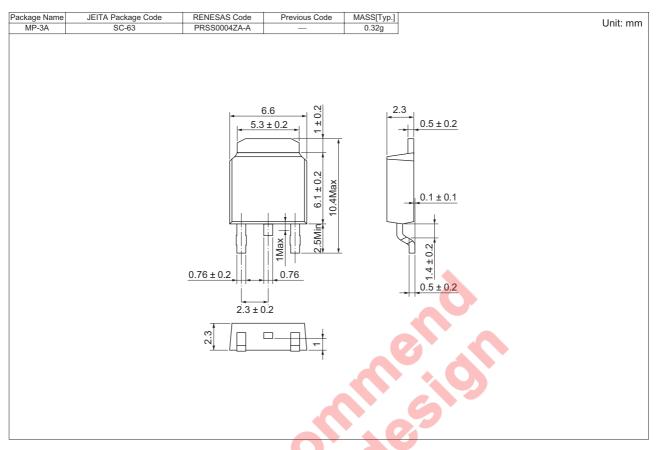








## **Package Dimensions**



### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX6ASJ-2-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX6ASJ-2

Note: Please confirm the specification about the shipping in detail.

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